

15th RD50 Workshop

Monday 16 November 2009

Defect Characterization - TE Auditorium (14:45 - 17:35)

time	[id] title	presenter
14:45	[26] The comparison of the defect generation during the proton irradiation in situ and afterwards in silicon	Prof. VAITKUS, Juozas
15:05	[11] INTERSTITIAL DEFECT REACTIONS IN P-TYPE SILICON IRRADIATED AT DIFFERENT TEMPERATURES	Dr MAKARENKO, Leonid
15:25	coffee break	
15:55	[27] The deep levels in the irradiated Si (WODEAN samples)	Prof. VAITKUS, Juozas
16:15	[21] Microscopic Study of Proton Irradiated Epitaxial Detectors	KHOMENKOV, Volodymyr
16:35	[28] Generation of a shallow donor after 6, 15 and 900 MeV electron irradiation	JUNKES, alexandra
16:55	[33] TSC studies on n- and p-type MCZ Si pad detectors irradiated with neutrons up to 10^{16} n/cm ²	SCARINGELLA, Monica
17:15	[29] Discussion: Wodean & Defect Characterization	